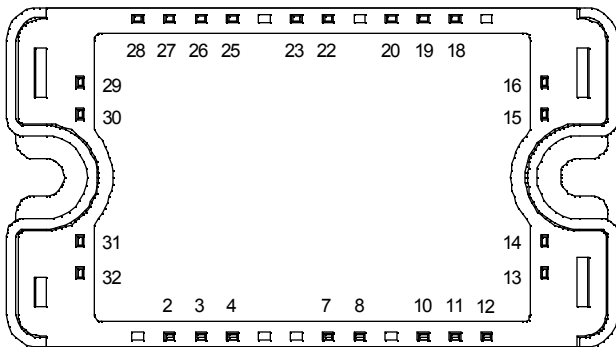
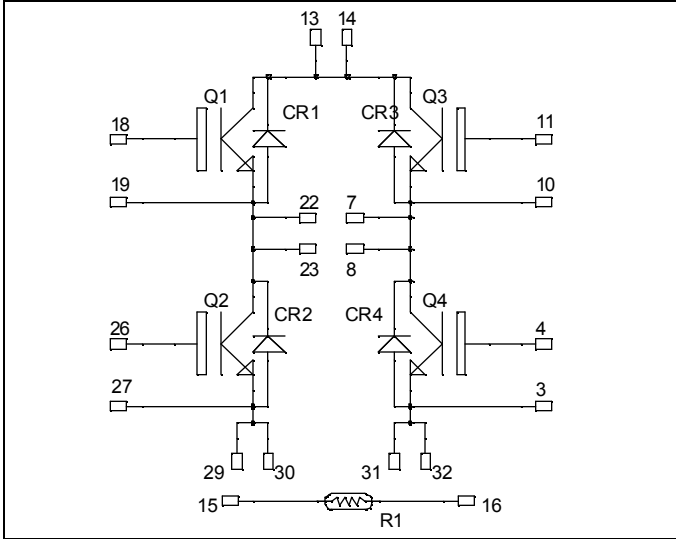


**Full - Bridge
Trench + Field Stop IGBT®
Power Module**

**$V_{CES} = 600V$
 $I_C = 30A @ T_c = 80^\circ C$**



All multiple inputs and outputs must be shorted together
Example: 13/14 ; 29/30 ; 22/23 ...

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	600	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	50
		$T_C = 80^\circ C$	30
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	60
V_{GE}	Gate - Emitter Voltage	±20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$	90
RBSOA	Reverse Bias Safe Operating Area	$T_J = 150^\circ C$	60A @ 550V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}, V_{CE} = 600\text{V}$			250	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 30\text{A}$	$T_j = 25^\circ\text{C}$	1.5	1.9	V
			$T_j = 150^\circ\text{C}$	1.7		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 400\mu\text{A}$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			300	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}$		1600		pF	
C_{oes}	Output Capacitance	$V_{CE} = 25\text{V}$		110			
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		50			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 30\text{A}$ $R_G = 15\Omega$		110		ns	
T_r	Rise Time			45			
$T_{d(off)}$	Turn-off Delay Time			200			
T_f	Fall Time			40			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 30\text{A}$ $R_G = 15\Omega$		120		ns	
T_r	Rise Time			50			
$T_{d(off)}$	Turn-off Delay Time			250			
T_f	Fall Time			60			
E_{on}	Turn-on Switching Energy			0.53			mJ
E_{off}	Turn-off Switching Energy			1.05			

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 600\text{V}$	$T_j = 25^\circ\text{C}$		250	μA
			$T_j = 150^\circ\text{C}$		500	
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle	$T_c = 80^\circ\text{C}$	30		A
V_F	Diode Forward Voltage	$I_F = 30\text{A}$ $V_{GE} = 0\text{V}$	$T_j = 25^\circ\text{C}$	1.6	2	V
			$T_j = 150^\circ\text{C}$	1.5		
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}$ $V_R = 300\text{V}$ $di/dt = 1800\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	120		ns
			$T_j = 150^\circ\text{C}$	210		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$	1.5		μC
			$T_j = 150^\circ\text{C}$	3.1		

Temperature sensor NTC (see application note APT0406 on www.advancedpower.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

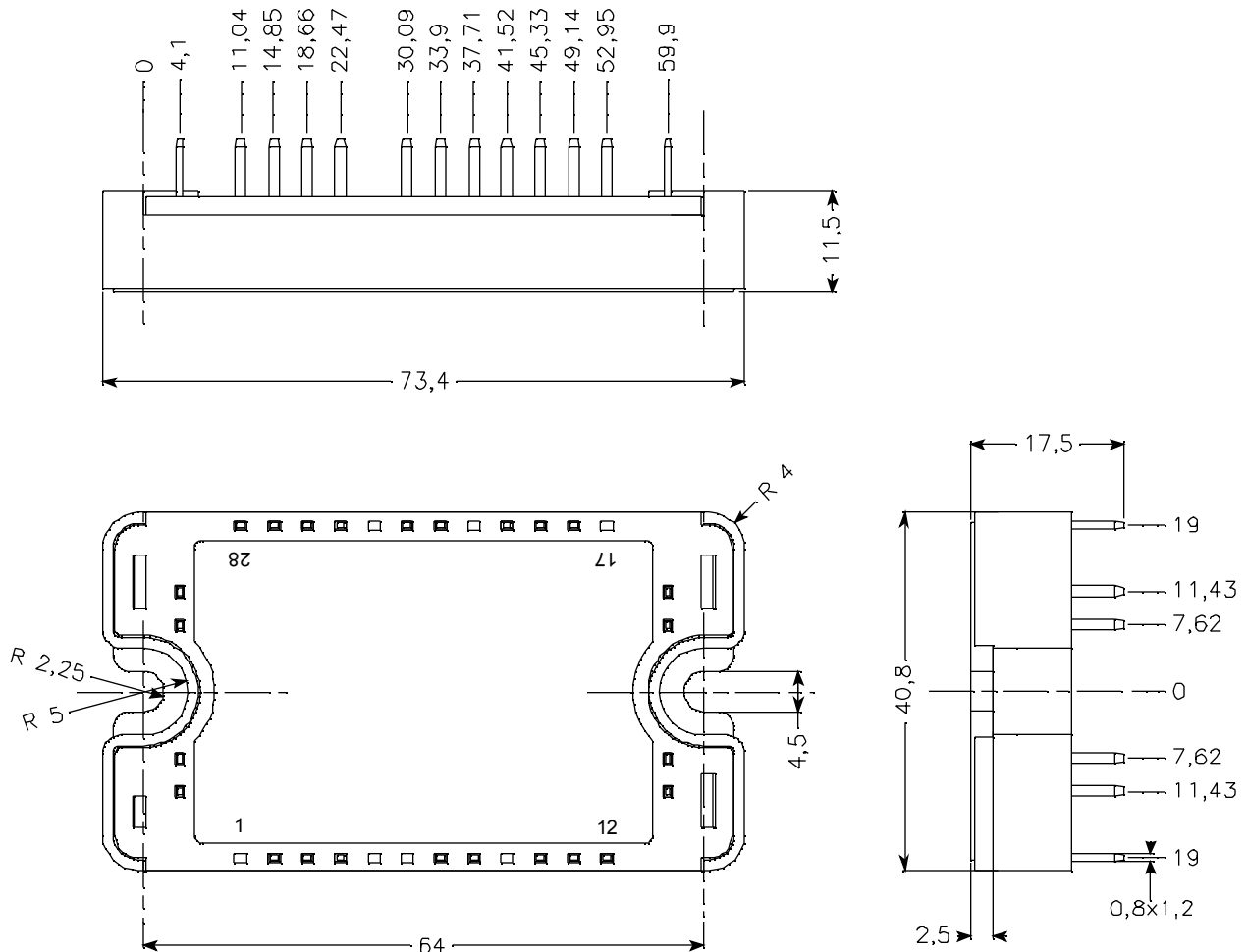
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T} - \frac{1}{T_{25}}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

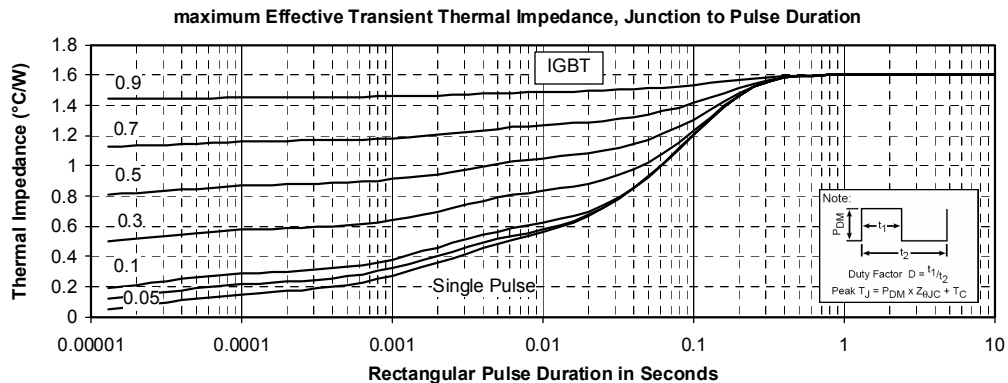
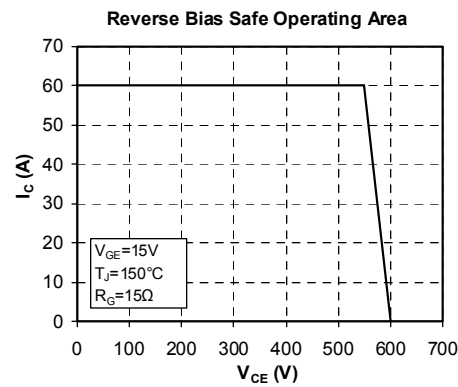
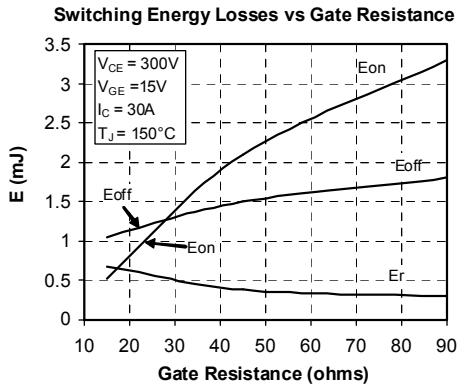
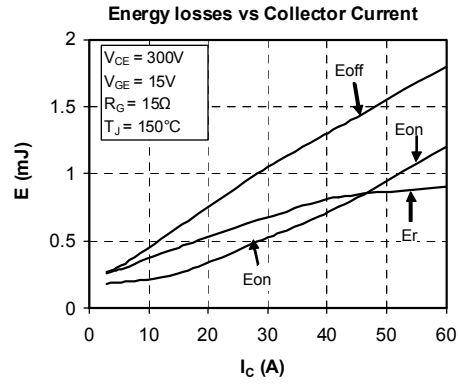
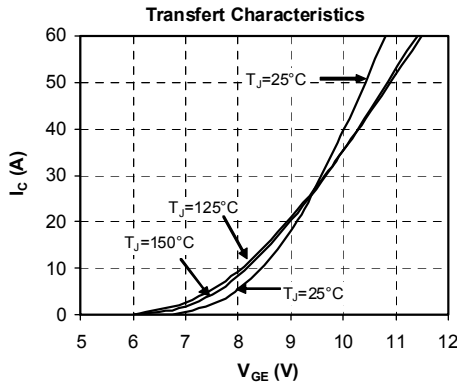
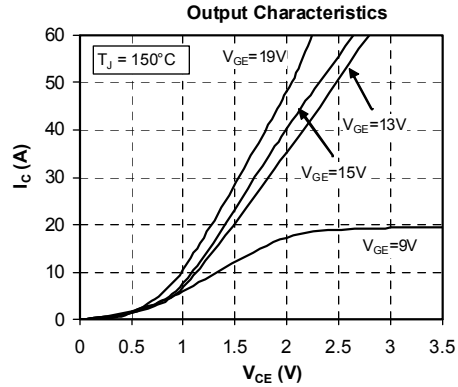
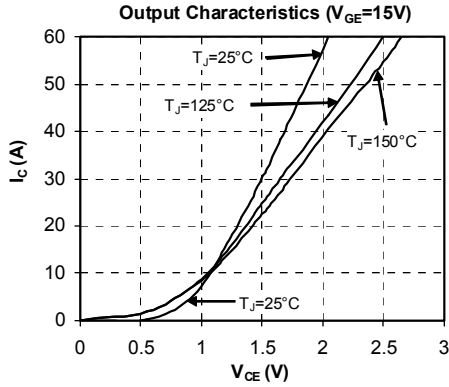
Thermal and package characteristics

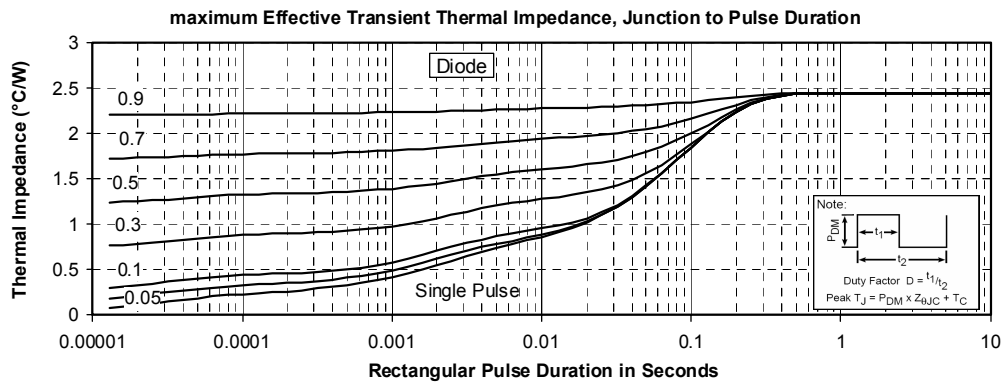
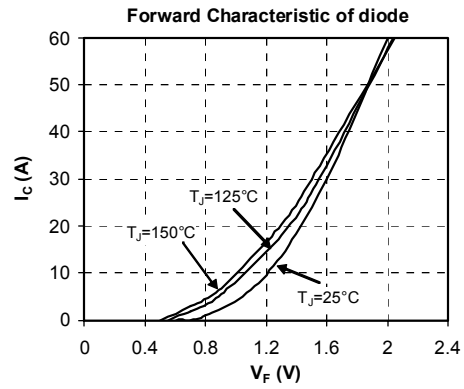
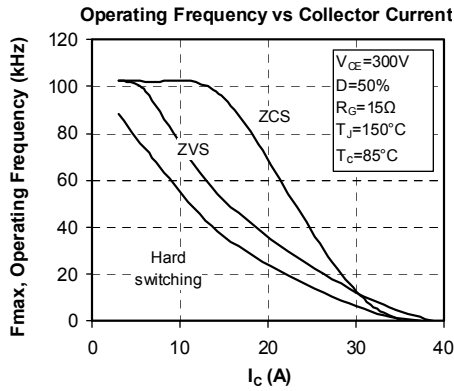
Symbol	Characteristic	Min	Typ	Max	Unit	
R _{thJC}	Junction to Case	IGBT		1.6	°C/W	
		Diode		2.45		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I _{isol} <1mA, 50/60Hz	2500			V	
T _J	Operating junction temperature range	-40		175	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	1.5	4.7	N.m
Wt	Package Weight				110	g

Package outline (dimensions in mm)



Typical Performance Curve





APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.